

THE SPECIFICATION OF AlGaAs IR LED CHIP “NR4JN33 “

1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is N-side up. The peak wavelength is 730 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (V_F) IF=20mA		1.80		V
Reverse Voltage (V_R) IR=10 μ A	5.0			V
Radiated Power ¹⁾ (P_o) IF=20mA	3.0			mW
Peak Wavelength (λ_p) IF=20mA		730		nm
Spectral Radiation Bandwidth ($\Delta\lambda$) IF=20mA		30		nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

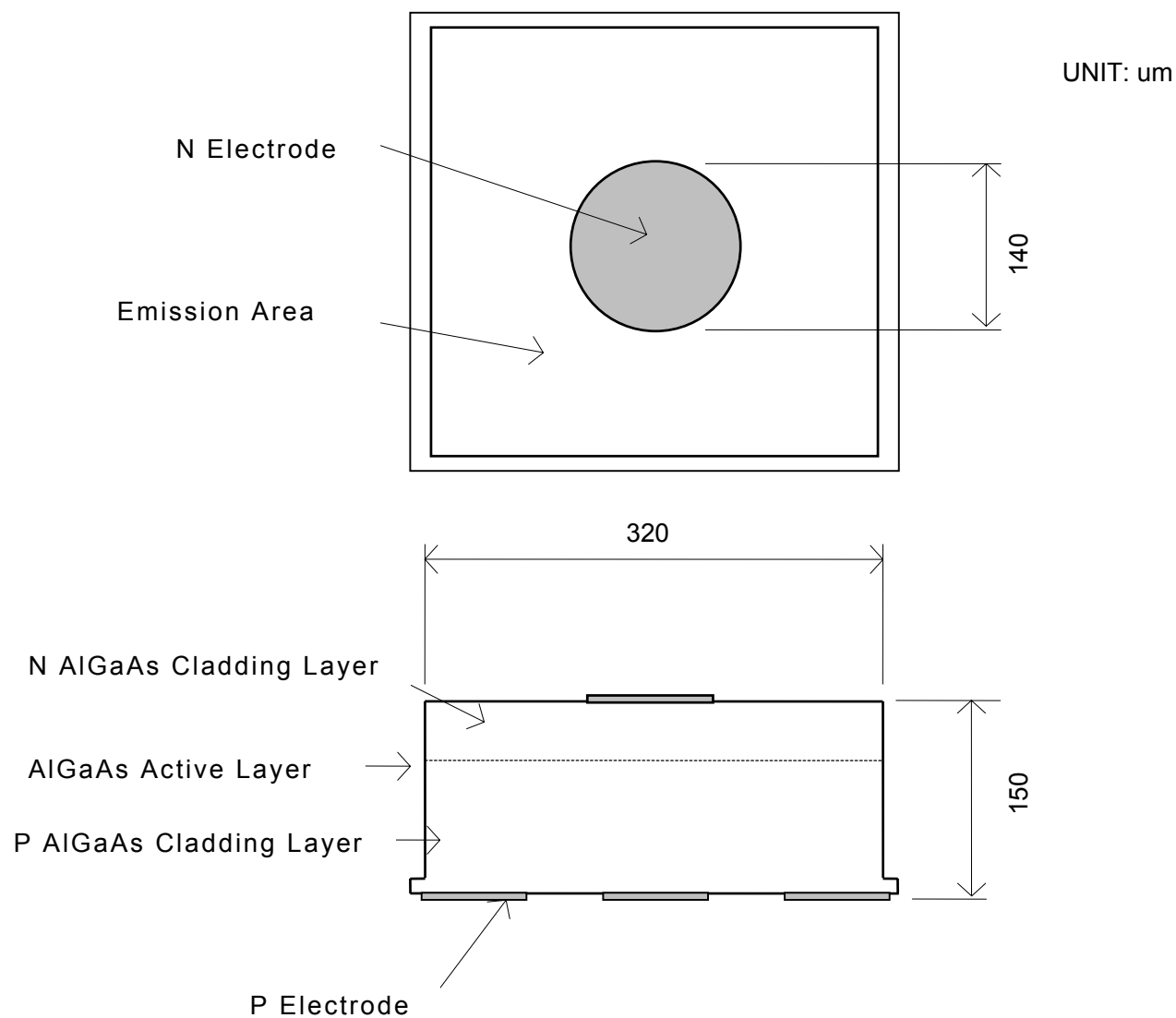
Storage Temperature
 while on mylar membrane : 0 to 40
 after removal from mylar membrane : -30 to 100

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

- 1)Material : AlGaAs
- 2)Structure : Double Hetero Structure
- 3)Junction Size : 0.320mmX0.320mm
- 4)Thickness : 0.150mm \pm 0.040mm
- 5)Bond Pad Size : 0.140mm diameter
- 6)Anode Metallization : Gold Alloy
- 7)Cathode Metallization: Gold Alloy

Physical Dimensions

Model NR4JN33



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.